

SKiiP® 3

2-pack-integrated intelligent Power System

Power section

SKiiP 2403GB172-4DW

Data

Power section features

- SKiiP technology inside
- Trench IGBTs
- CAL diode technology
- Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP® 3 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized file no. E63532

1) with assembly of suitable MKP capacitor per terminal

8) AC connection busbars must be connected by the user; copper busbars available on request

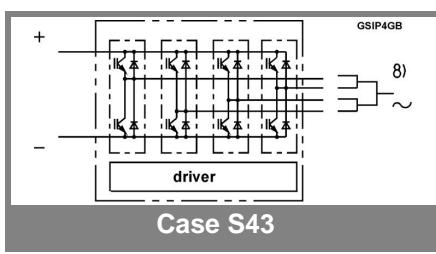
Absolute Maximum Ratings		$T_s = 25^\circ\text{C}$ unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}		1700		V
$V_{CC}^{1)}$	Operating DC link voltage	1200		V
V_{GES}		± 20		V
I_C	$T_s = 25 \text{ (70)}^\circ\text{C}$	2400 (1800)		A
Inverse diode				
$I_F = -I_C$	$T_s = 25 \text{ (70)}^\circ\text{C}$	1800 (1400)		A
I_{FSM}	$T_j = 150^\circ\text{C}$, $t_p = 10 \text{ ms}$; sin.	13500		A
I^2t (Diode)	Diode, $T_j = 150^\circ\text{C}$, 10 ms	911		kA²s
T_j (T_{stg})		- 40 ... + 150 (125)		°C
V_{isol}	rms, AC, 1 min, main terminals to heat sink	4000		V
$I_{AC\text{-terminal}}$	per AC terminal, rms, $T_s = 70^\circ\text{C}$,	400		A
	$T_{\text{terminal}} < 115^\circ\text{C}$			

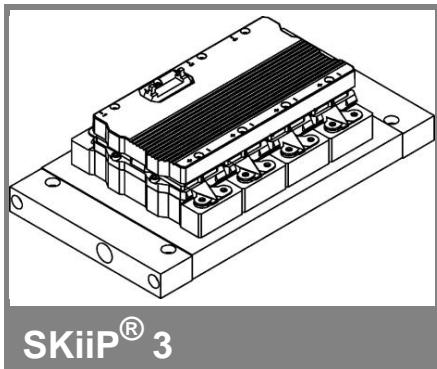
Characteristics		$T_s = 25^\circ\text{C}$ unless otherwise specified		
Symbol	Conditions	min.	typ.	max.
IGBT				
V_{CEsat}	$I_C = 1200 \text{ A}$, $T_j = 25 \text{ (125)}^\circ\text{C}$; measured at terminal	1,9 (2,2)	2,4	V
V_{CEO}	$T_j = 25 \text{ (125)}^\circ\text{C}$; at terminal	1 (0,9)	1,2 (1,1)	V
r_{CE}	$T_j = 25 \text{ (125)}^\circ\text{C}$; at terminal	0,8 (1)	1 (1,3)	mΩ
I_{CES}	$V_{GE} = 0 \text{ V}$, $V_{CE} = V_{CES}$, $T_j = 25 \text{ (125)}^\circ\text{C}$	4,8 (288)		mA
$E_{on} + E_{off}$	$I_C = 1200 \text{ A}$, $V_{CC} = 900 \text{ V}$ $T_j = 125^\circ\text{C}$, $V_{CC} = 1200 \text{ V}$	780		mJ
$R_{CC+EE'}$	terminal chip, $T_j = 25^\circ\text{C}$	0,13		mΩ
L_{CE}	top, bottom	3		nH
C_{CHC}	per phase, AC-side	4		nF
Inverse diode				
$V_F = V_{EC}$	$I_F = 1200 \text{ A}$, $T_j = 25 \text{ (125)}^\circ\text{C}$ measured at terminal	2 (1,8)	2,15	V
V_{TO}	$T_j = 25 \text{ (125)}^\circ\text{C}$	1,1 (0,8)	1,2 (0,9)	V
r_T	$T_j = 25 \text{ (125)}^\circ\text{C}$	0,8 (0,8)	0,8 (0,9)	mΩ
E_{rr}	$I_C = 1200 \text{ A}$, $V_{CC} = 900 \text{ V}$ $T_j = 125^\circ\text{C}$, $V_{CC} = 1200 \text{ V}$	144		mJ
		171		mJ
Mechanical data				
M_{dc}	DC terminals, SI Units	6	8	Nm
M_{ac}	AC terminals, SI Units	13	15	Nm
w	SKiiP® 3 System w/o heat sink	3,1		kg
w	heat sink	6,2		kg

Thermal characteristics (NWK 40; 8l/min; 50%glyc.); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc. IEC 60747-15)

$R_{th(j-s)I}$	per IGBT	0,013	K/W
$R_{th(j-s)D}$	per diode	0,025	K/W
Z_{th}	R_i (mK/W) (max. values)	$\tau_{au}(s)$	
	1 2 3 4	1	2 3 4
$Z_{th(j-r)I}$	1,2 5 5,8 0	69	0,35 0,02 1
$Z_{th(j-r)D}$	2 3 13,5 13,5	50	5 0,25 0,04
$Z_{th(r-a)}$	2,7 4,6 1,1 0,6	48	15 2,8 0,4

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.





2-pack-integrated intelligent Power System

**2-pack
integrated gate driver
SKiiP 2403GB172-4DW**

Data

Gate driver features

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- Short circuit protection
- Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 60068-1 (climate) 40/85/56
- UL recognized file no. 242581

Absolute Maximum Ratings		$T_a = 25^\circ\text{C}$ unless otherwise specified	
Symbol	Conditions	Values	Units
V_{S2}	unstabilized 24 V power supply	30	V
V_i	input signal voltage (high)	15 + 0,3	V
dv/dt	secondary to primary side	75	kV/ μs
V_{isolIO}	input / output (AC, rms, 2s)	4000	V
V_{isolPD}	partial discharge extinction voltage, rms, $Q_{PD} \leq 10 \text{ pC}$	1500	V
V_{isol12}	output 1 / output 2 (AC, rms, 2s)	1500	V
f_{sw}	switching frequency	7	kHz
f_{out}	output frequency for $I_{peak(1)}=I_C$	7	kHz
$T_{op} (T_{stg})$	operating / storage temperature	- 40 ... + 85	°C

Characteristics $(T_a = 25^\circ\text{C})$				
Symbol	Conditions	min.	typ.	max.
V_{S2}	supply voltage non stabilized	13	24	30
I_{S2}	$V_{S2} = 24 \text{ V}$	$430+45*f/\text{kHz}+0,00011*(I_{AC}/A)^2$		
V_{IT+}	input threshold voltage (High)	12,3		
V_{IT-}	input threshold voltage (Low)	4,6		
R_{IN}	input resistance	10		
C_{IN}	input capacitance	1		
$t_{d(on)IO}$	input-output turn-on propagation time	1,3		
$t_{d(off)IO}$	input-output turn-off propagation time	1,3		
$t_{pERRRESET}$	error memory reset time	9		
t_{TD}	top / bottom switch interlock time	3,3		
$I_{analogOUT}$	max. 5mA; 8 V corresponds to 15 V supply voltage for external components	2000		
I_{s1out}	max. load current	50		
I_{TRIPSC}	over current trip level ($I_{analog OUT} = 10 \text{ V}$)	2500		
T_{tp}	over temperature protection	110	120	
U_{DCTRIP}	$U_{DC}-\text{protection}$ ($U_{analog OUT} = 9 \text{ V}$); (option for GB types)	not implemented		

For electrical and thermal design support please use SEMISEL.
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